

PATENT

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ABSTRACT OF THE DISCLOSURE

A silicon oxide layer is produced by plasma enhanced decomposition of an organosilicon compound to deposit films having a carbon content of at least 1% by atomic weight. An optional carrier gas may be introduced to facilitate the deposition process at a flow rate less than or equal to the flow rate of the organosilicon compounds. An oxygen rich surface may be formed adjacent the silicon oxide layer by temporarily increasing oxidation of the organosilicon compound.

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